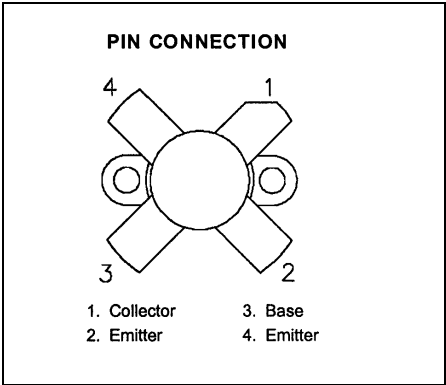
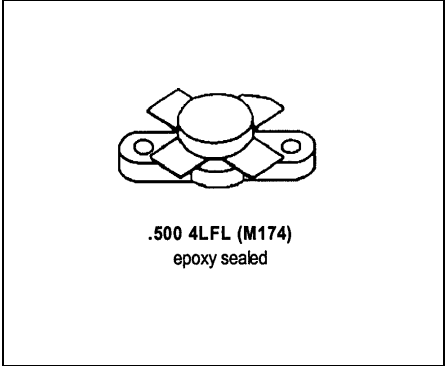


# MS1078

## RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

### Features

- Optimized for SSB
- 30 MHz
- 28 Volts
- IMD -30dB
- Common Emitter
- Gold Metallization
- P<sub>OUT</sub> = 130 W PEP
- G<sub>P</sub> = 12 dB Gain



### DESCRIPTION:

The MS1078 is a Class AB 28V epitaxial silicon NPN planar transistor designed primarily for SSB communications. The MS1078 utilizes emitter ballasting for superior ruggedness and reliability under extreme operating conditions.

### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	70	V
V <sub>CEO</sub>	Collector-Emitter Voltage	35	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>C</sub>	Device Current	12	A
P <sub>DISS</sub>	Power Dissipation	175	W
T <sub>J</sub>	Junction Temperature	+200	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

### Thermal Data

R <sub>TH(J-C)</sub>	Thermal Resistance Junction-case	1.0	°C/W
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**ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)**  
**STATIC**

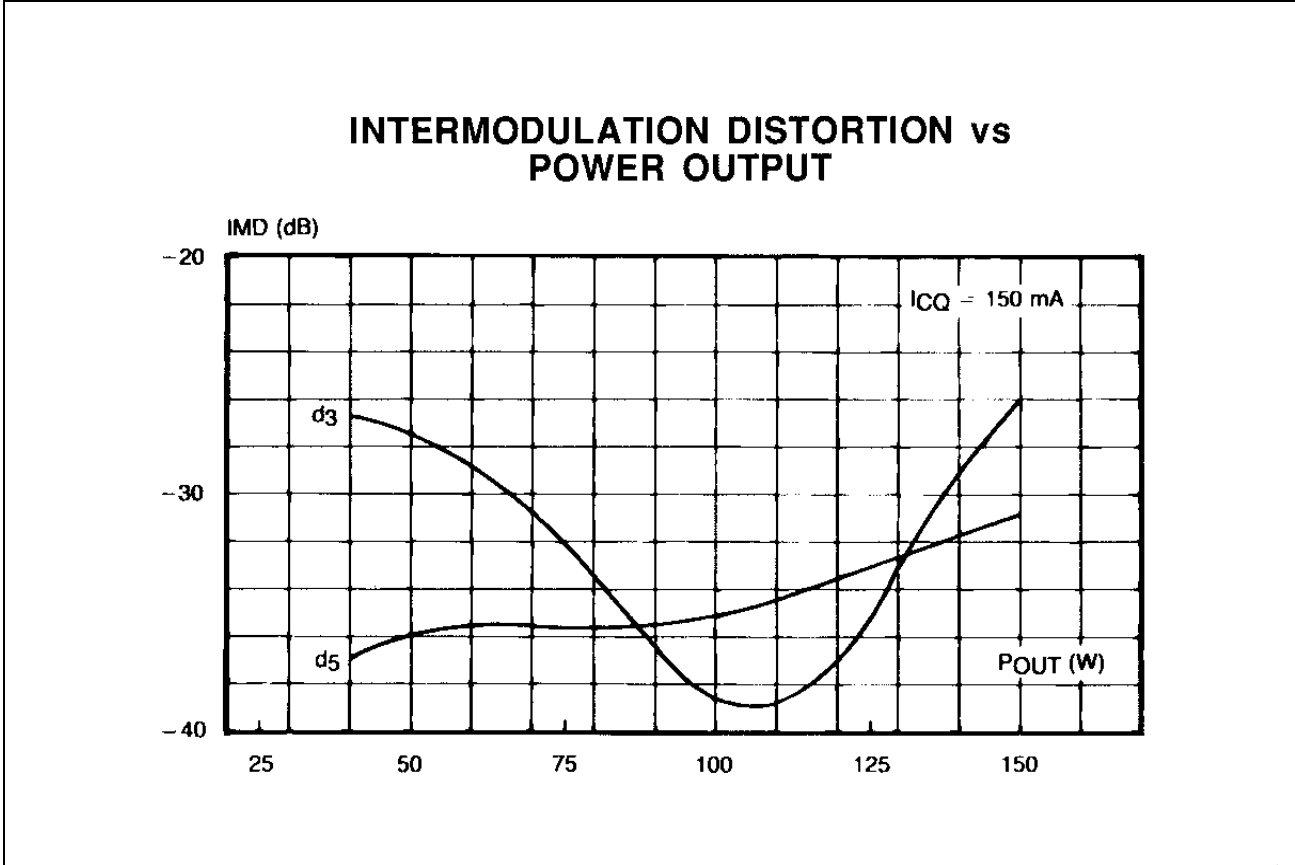
Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
<b>BV<sub>CES</sub></b>	<b>I<sub>C</sub> = 50 mA    V<sub>BE</sub> = 0 V</b>	<b>110</b>			<b>V</b>
<b>BV<sub>CEO</sub></b>	<b>I<sub>C</sub> = 100 mA    I<sub>B</sub> = 0 mA</b>	<b>55</b>			<b>V</b>
<b>BV<sub>EBO</sub></b>	<b>I<sub>E</sub> = 20 mA    I<sub>C</sub> = 0 mA</b>	<b>4.0</b>			<b>V</b>
<b>I<sub>CES</sub></b>	<b>V<sub>CE</sub> = 35 V    I<sub>E</sub> = 0 mA</b>			<b>20</b>	<b>mA</b>
<b>h<sub>FE</sub></b>	<b>V<sub>CE</sub> = 5 V    I<sub>C</sub> = 7 A</b>	<b>18</b>		<b>50</b>	

**DYNAMIC**

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
<b>P<sub>OUT</sub></b>	<b>f = 30 MHz    V<sub>CE</sub> = 28 V    I<sub>CQ</sub> = 150 mA</b>	<b>130</b>			<b>W</b>
<b>G<sub>P</sub></b>	<b>P<sub>OUT</sub> = 130 W PEP    V<sub>CE</sub> = 28 V    I<sub>CQ</sub> = 150 mA</b>	<b>12</b>			<b>dB</b>
<b>IMD *</b>	<b>P<sub>OUT</sub> = 130 W PEP    V<sub>CE</sub> = 28 V    I<sub>CQ</sub> = 150 mA</b>			<b>-30</b>	<b>dBc</b>
<b>η<sub>C</sub></b>	<b>P<sub>OUT</sub> = 130 W PEP    V<sub>CE</sub> = 28 V    I<sub>CQ</sub> = 150 mA</b>	<b>37</b>			<b>%</b>
<b>C<sub>OB</sub></b>	<b>f = 1 MHz    V<sub>CB</sub> = 28 V</b>			<b>250</b>	<b>pF</b>

Note: \* f<sub>1</sub> = 30.00 MHz, f<sub>2</sub> = 30.01 MHz

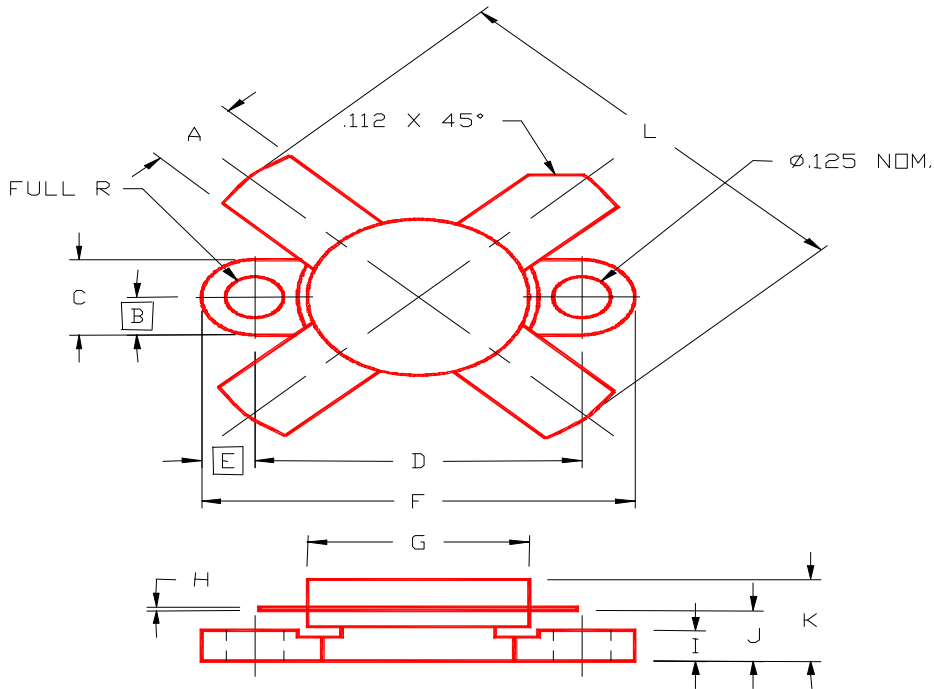
**TYPICAL PERFORMANCE**



MS1078

**PACKAGE MECHANICAL DATA**

**PACKAGE STYLE M174**



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.220/5,59	.230/5,84	I	.090/2,29	.110/2,79
B	.125/3,18		J	.160/4,06	.175/4,45
C	.245/6,22	.255/6,48	K		.280/7,11
D	.720/18,28	.730/18,54	L		1.050/26,67
E	.125/3,18				
F	.970/24,64	.980/24,89			
G	.495/12,57	.505/12,83			
H	.003/0,08	.007/0,18			